

### AMENDMENT TO THE CLAIMS

Please **ADD** claims 16 and 17 as shown below.

Please **AMEND** claims 5-9 as shown below.

The following is a listing of the claims in this application:

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1. (Previously Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:  
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

c\ 2. (Original) The method of Claim 1, including supplying germanium precursor to the substrate.

3. (Original) The method of Claim 1, wherein the film has a dopant content of about  $1 \times 10^{17}$  to  $1 \times 10^{21} / \text{cm}^3$ .

4. (Original) The method of Claim 1, wherein the doping is at a temperature of less than 800°C.

5. (Currently Amended) The A method according to claim 1, wherein the dopant is carbon.

6. (Currently Amended) The A method according to claim 2, wherein the dopant is carbon..

7. (Currently Amended) The A method according to claim 6, wherein the carbon doping is by a carbon precursor supply that is a single source.

8. (Currently Amended) The A method according to claim 2, wherein the film has a germanium content of 1 to 30% by weight.

9. (Currently Amended) The A method according to Claim 1, wherein the silicon precursor is silane supplied at a partial pressure in a range of about 0.1 to 10 millitorr.

10-14 (Withdrawn).

15. (Previously Amended) A method of growing a film without sharp pressure transitions, comprising:

cl carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduce pressure of about 0.1 to 100 millitorr.

16 (Added) The method of claim 1, wherein the step of carbon or boron doping comprised carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

17. (Added) The method of claim 15, wherein the step of carbon or boron-doping comprises carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

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